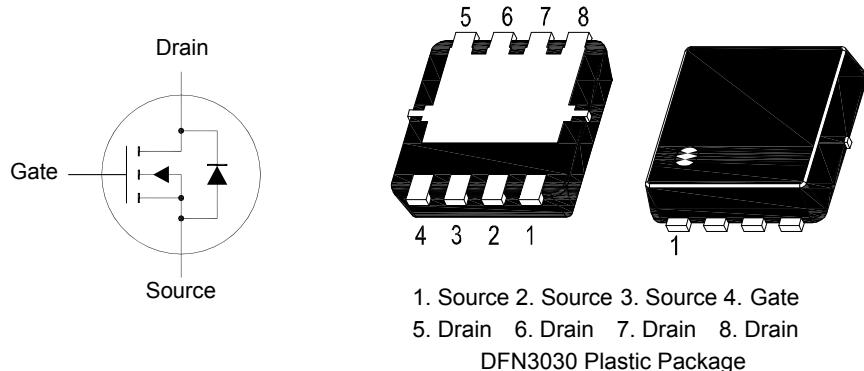


SFTN7210MP

N-Channel Enhancement Mode MOSFET



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Drain-Gate Voltage	V_{GS}	± 20	V
Drain Current - Continuous	I_D	50 39	A
Drain Current - Continuous	I_{DSM}	30 24	A
Power Dissipation	P_D	83 33	W
Power Dissipation ¹⁾	P_{DSM}	6.2 4	W
Drain Current - Pulsed	I_{DM}	250	A
Avalanche energy L=0.1mH	E_{AS}	101	mJ
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance - Junction to Ambient ¹⁾ $t \leq 10s$	$R_{\theta JA}$	20	°C/W
Thermal Resistance - Junction to Ambient ¹⁾ Steady-State	$R_{\theta JA}$	55	°C/W
Thermal Resistance - Junction to Case	$R_{\theta JC}$	1.5	°C/W

¹⁾ The value of $R_{\theta JA}$ is measured with the device mounted on 1in ² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ $t \leq 10s$ value and the maximum allowed junction temperature of $150^\circ C$. The value in any given application depends on the user's specific board design, and the maximum temperature of $150^\circ C$ may be used if the PCB allows it.

SFTN7210MP

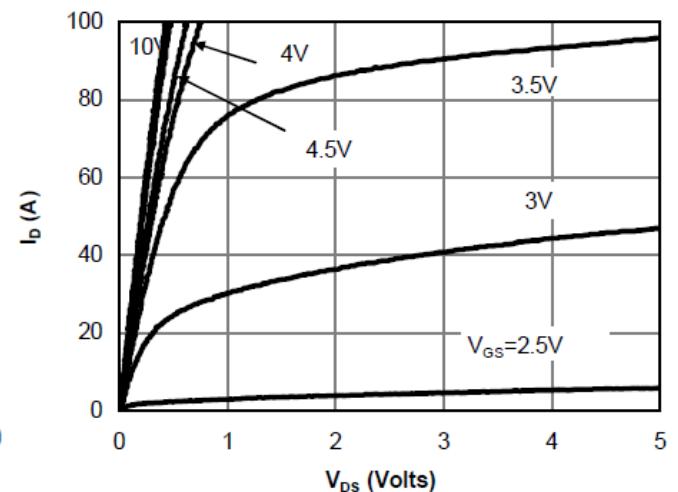
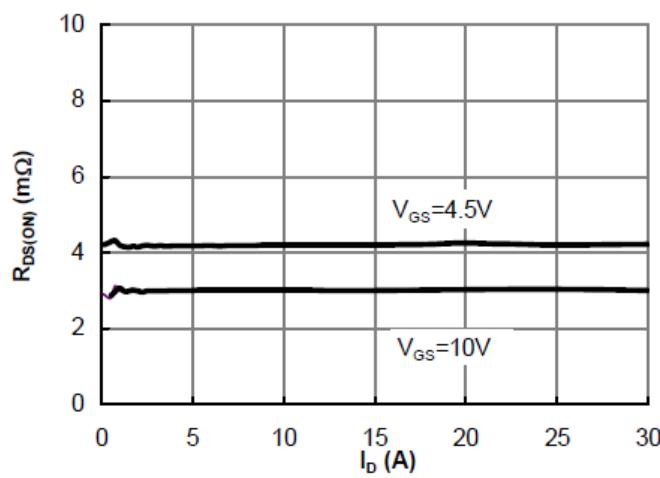
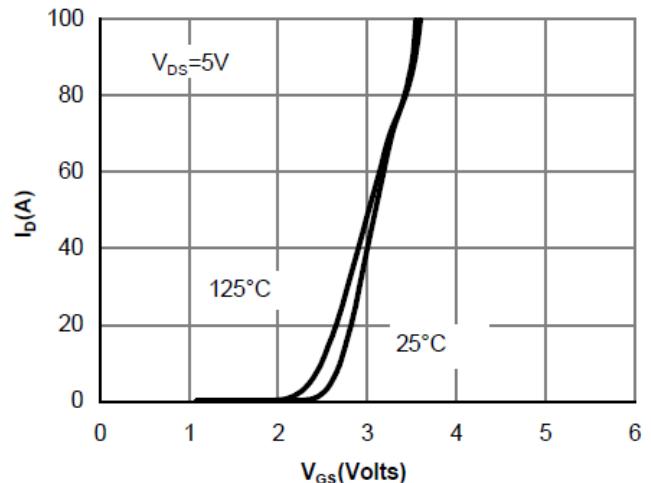
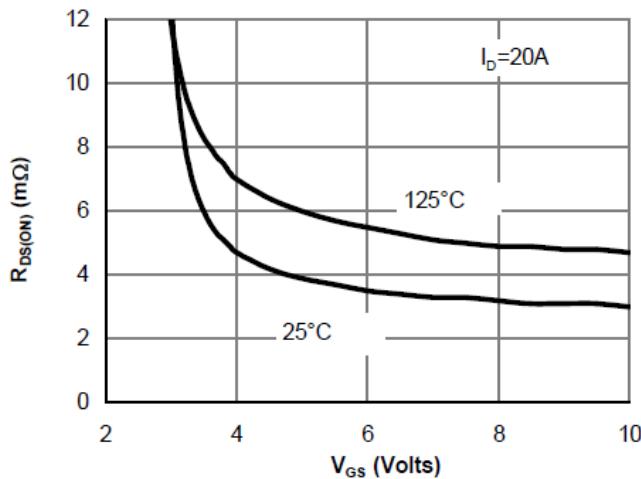
Characteristics at $T_j = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	BV_{DSS}	30	-	-	V
Gate-Source Threshold Voltage at $V_{\text{DS}} = V_{\text{GS}}$, $I_D = 250 \mu\text{A}$	V_{GSt}	1.3	-	2.3	V
Drain-Source Leakage Current at $V_{\text{DS}} = 30 \text{ V}$ at $V_{\text{DS}} = 30 \text{ V}, T_j = 55^\circ\text{C}$	I_{DSS}	- -	- -	1 5	μA
Gate-Source Leakage Current at $V_{\text{GS}} = \pm 20 \text{ V}$	I_{GSS}	-	-	100	nA
Drain-Source On-State Resistance at $V_{\text{GS}} = 10 \text{ V}$, $I_D = 20 \text{ A}$ at $V_{\text{GS}} = 10 \text{ V}$, $I_D = 20 \text{ A}$, $T_j = 125^\circ\text{C}$ at $V_{\text{GS}} = 4.5 \text{ V}$, $I_D = 20 \text{ A}$	$R_{\text{DS(on)}}$	- - -	- - -	4 6.2 5.8	$\text{m}\Omega$
Forward Transconductance at $V_{\text{DS}} = 5 \text{ V}$, $I_D = 20 \text{ A}$	g_{FS}	-	105	-	S
Input Capacitance at $V_{\text{GS}} = 0 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	-	2380	pF
Output Capacitance at $V_{\text{GS}} = 0 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	-	940	pF
Reverse Transfer Capacitance at $V_{\text{GS}} = 0 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	-	95	pF
Turn-On Delay Time at $V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $R_L = 0.75 \Omega$, $R_{\text{GEN}} = 3 \Omega$	$t_{\text{d(on)}}$	-	7.3	-	ns
Turn-On Rise Time at $V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $R_L = 0.75 \Omega$, $R_{\text{GEN}} = 3 \Omega$	t_r	-	3.7	-	ns
Turn-Off Delay Time at $V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $R_L = 0.75 \Omega$, $R_{\text{GEN}} = 3 \Omega$	t_{off}	-	21.2	-	ns
Turn-Off Fall Time at $V_{\text{GS}} = 10 \text{ V}$, $V_{\text{DS}} = 15 \text{ V}$, $R_L = 0.75 \Omega$, $R_{\text{GEN}} = 3 \Omega$	t_f	-	3.3	-	ns

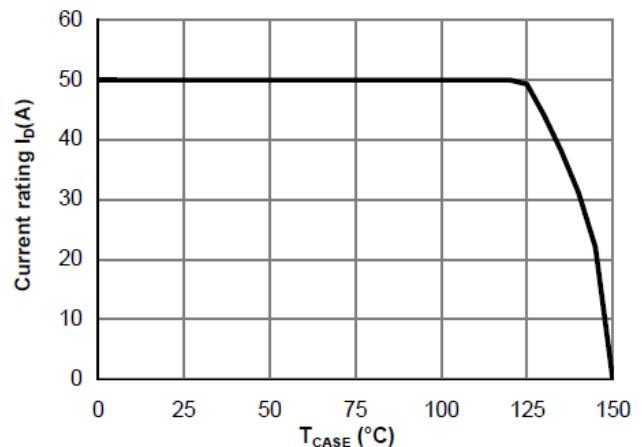
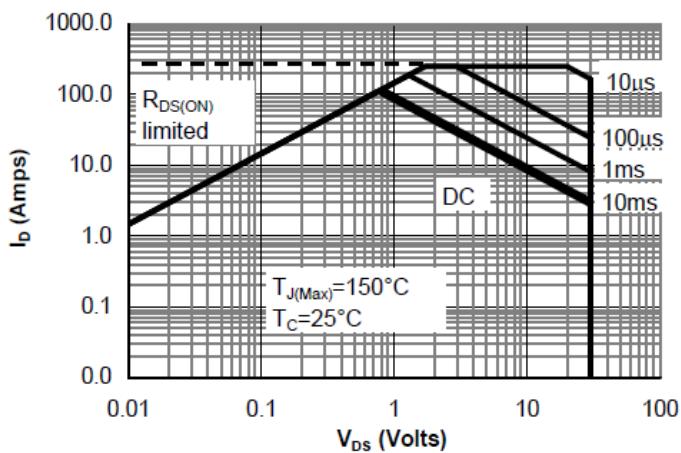
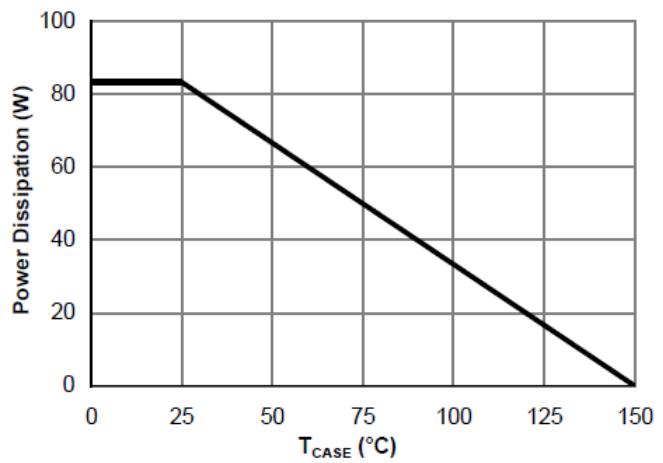
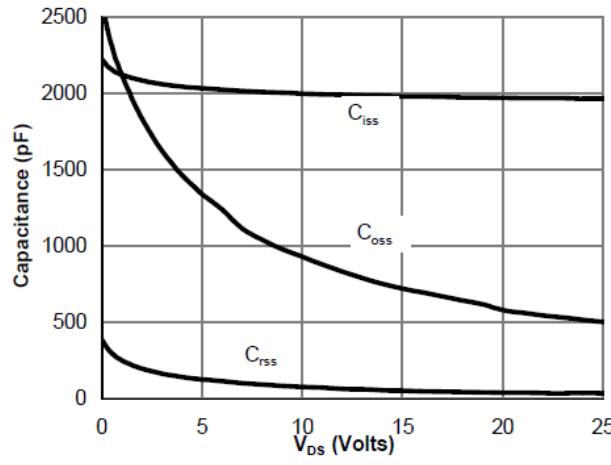
Drain-Source Diode Characteristics and Maximum Ratings

Parameter	Symbol	Max.	Unit
Drain-Source Diode Forward Voltage at $V_{\text{GS}} = 0 \text{ V}$, $I_S = 1 \text{ A}$	V_{SD}	1	V

SFTN7210MP

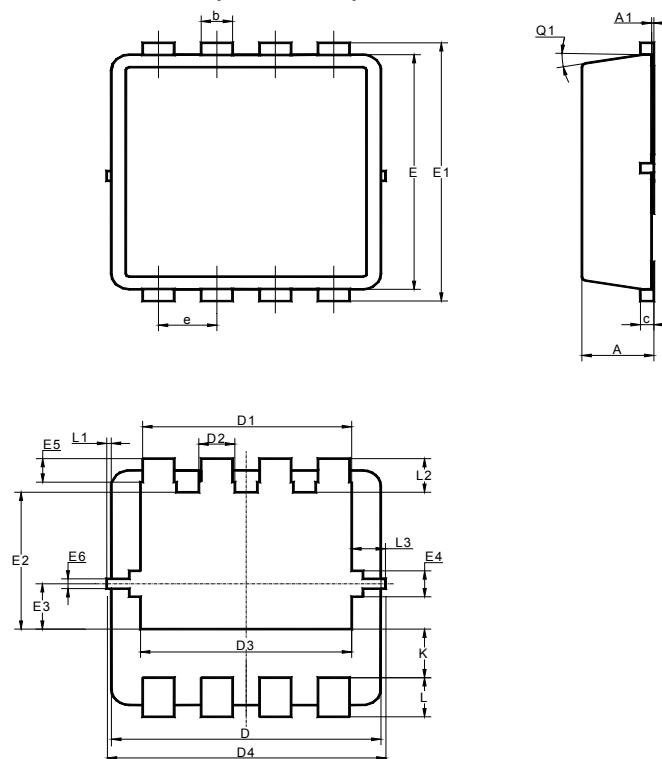


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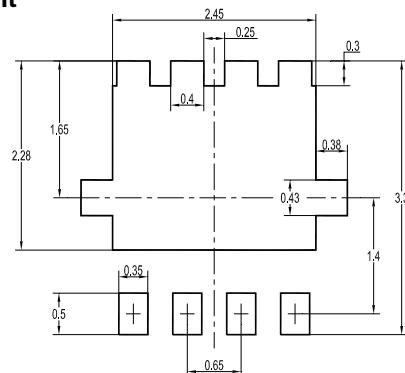
DFN3030 Package Outline Dimensions (Units: mm)



UNIT	A	A1	b	c	D	D1	D2	D3	D4	E	E1	E2	E3
mm	0.9	0.05	0.35	0.25	3.1	2.45	0.5	2.7	3.2	3.1	3.3	1.85	0.68
	0.7	0	0.24	0.1	2.9	2.2	0.3	2.4	3	2.9	3.1	1.65	0.48

UNIT	E4	E5	E6	e	K	L	L1	L2	L3	Q1
mm	0.43	0.4	0.25	0.7	0.72	0.5	0.1	0.53	0.475	12°
	0.23	0.2	0.075	0.6	0.52	0.3	0	0.33	0.275	0°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN3030	8	4 ± 0.1	0.157 ± 0.004	330	13	3,000

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